

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
-20V	50mΩ @V <sub>GS</sub> = -4.5V	-4.5A
	100mΩ @V <sub>GS</sub> = -2.5V	-3.2A

## Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at <https://www.diodes.com/products/automotive/automotive-products/>.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. <https://www.diodes.com/quality/product-definitions/>**

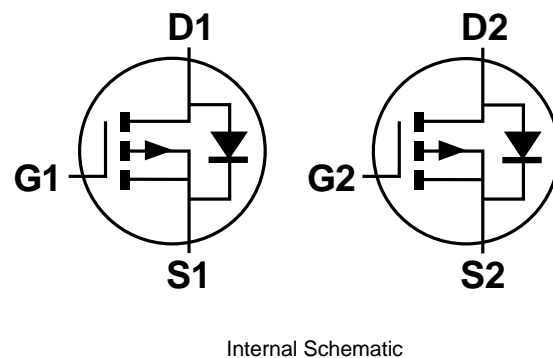
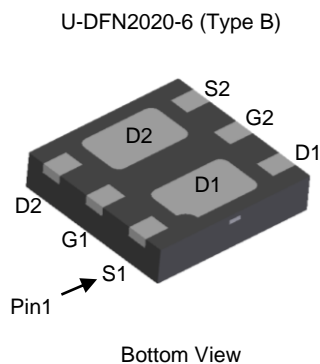
## Description and Applications

This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

## Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208④
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)



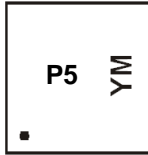
## Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2065UFDB-7	U-DFN2020-6 (Type B)	3,000/Tape & Reel
DMP2065UFDB-13	U-DFN2020-6 (Type B)	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

**Marking Information**

Site 1



P5 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: H = 2020)  
 M = Month (ex: 9 = September)

Date Code Key

Year	2016	...	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	D	...	H	I	J	K	L	M	N	O	P	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Site 2



P5 = Product Type Marking Code  
 YWX = Date Code Marking  
 Y = Year (ex: 0 = 2020)  
 W = Week (ex: a = Week 27; z Represents Week 52 and 53)  
 X = Internal Code (ex: U = Monday)

Date Code Key

Year	2016	...	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	6	...	0	1	2	3	4	5	6	7	8	9
Week	1-26			27-52			53					
Code	A-Z			a-z			z					
Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat					
Code	T	U	V	W	X	Y	Z					

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-20	V
Gate-Source Voltage			V <sub>GSS</sub>	±12	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = -4.5V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	-4.5	A
		T <sub>A</sub> = +85°C		-3.6	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	-25	A
Maximum Continuous Body Diode Forward Current (Note 6)			I <sub>S</sub>	-1.4	A
Avalanche Current (Note 7) L = 0.1mH			I <sub>AS</sub>	-13	A
Avalanche Energy (Note 7) L = 0.1mH			E <sub>AS</sub>	9	mJ

**Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	P <sub>D</sub>	0.74	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θJA</sub>	171	°C/W
	t < 10s		131	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.54	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	82	°C/W
	t < 10s		60	
Thermal Resistance, Junction to Case (Note 6)		R <sub>θJC</sub>	13	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1.0	µA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.4	—	-1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	40	50	mΩ	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -2.0A
			55	100		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -2.0A
			75	150		V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -1.6A
			95	200		V <sub>GS</sub> = -1.5V, I <sub>D</sub> = -1.0A
Diode Forward Voltage	V <sub>SD</sub>	—	-0.75	-1.1	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	752	—	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	87	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	78	—	pF	
Gate Resistance	R <sub>G</sub>	—	15.2	—	Ω	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V, f = 1.0MHz
Total Gate Charge	Q <sub>g</sub>	—	9.1	—	nC	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -4V, I <sub>D</sub> = -3.5A
Gate-Source Charge	Q <sub>gs</sub>	—	1.2	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	1.9	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	5.4	—	ns	V <sub>DS</sub> = -4V, V <sub>GS</sub> = -4.5V, R <sub>G</sub> = 6Ω, I <sub>D</sub> = -1A
Turn-On Rise Time	t <sub>R</sub>	—	8.3	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	47	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	20	—	ns	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

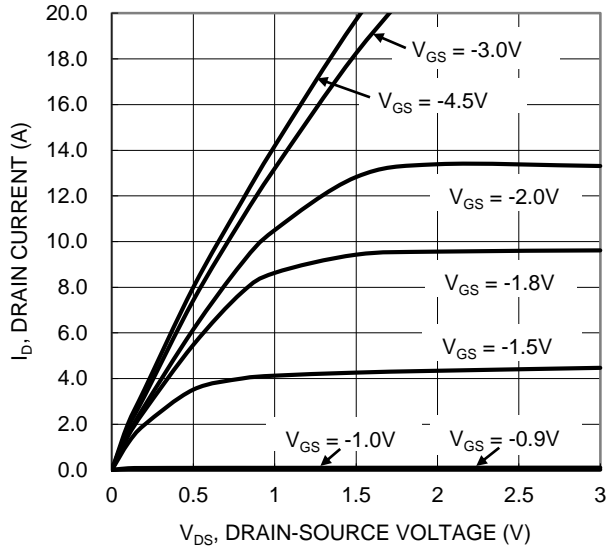


Figure 1. Typical Output Characteristic

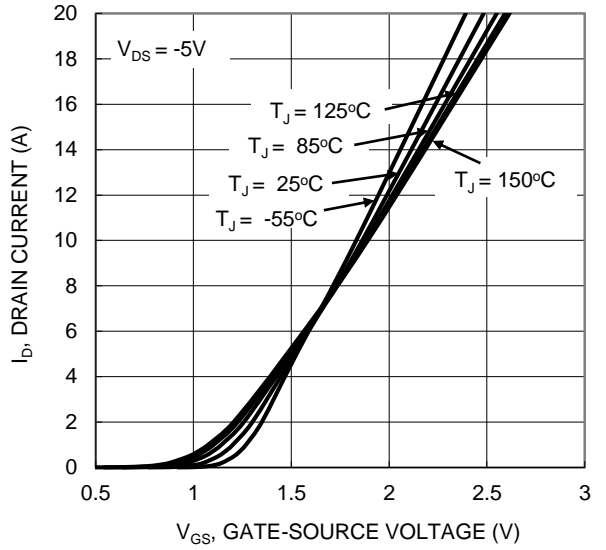


Figure 2. Typical Transfer Characteristic

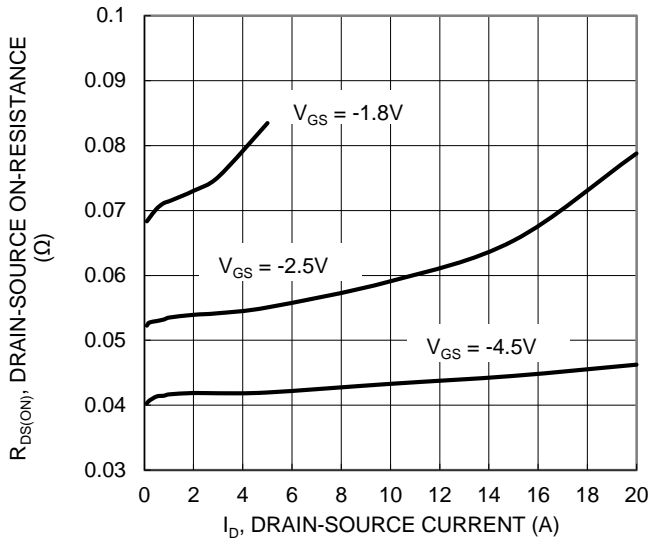


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

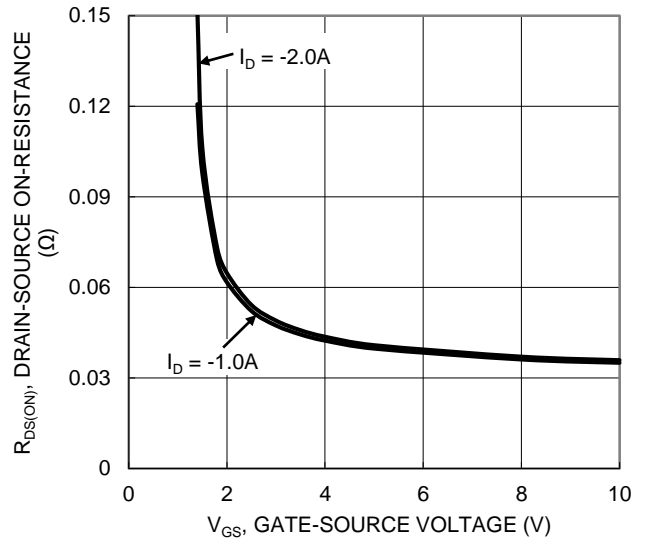


Figure 4. Typical Transfer Characteristic

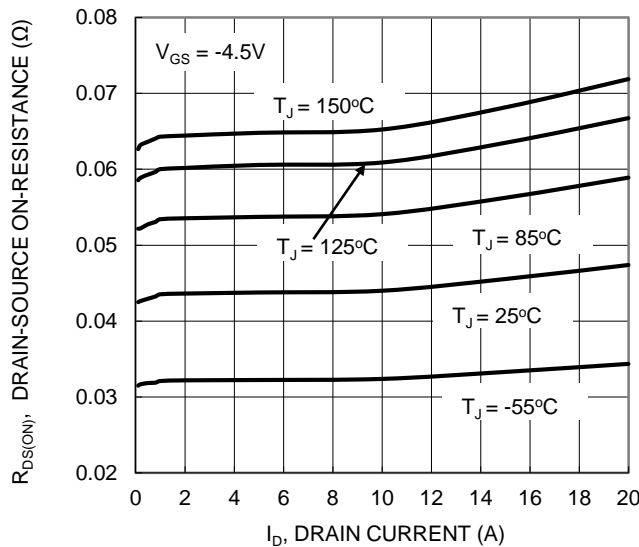


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

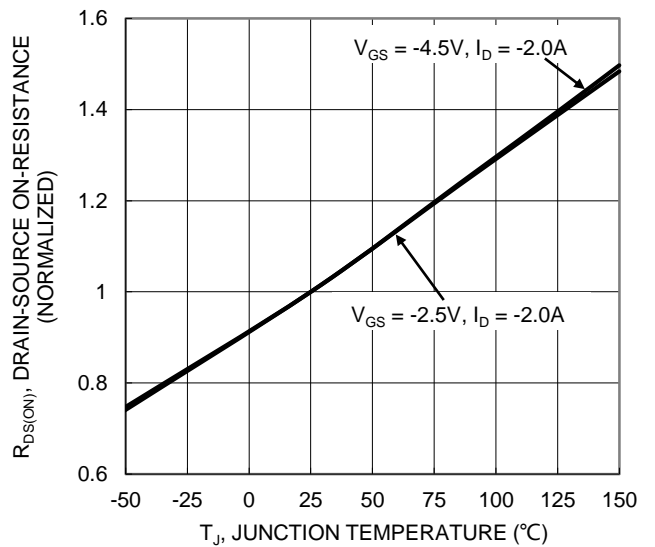


Figure 6. On-Resistance Variation with Junction Temperature

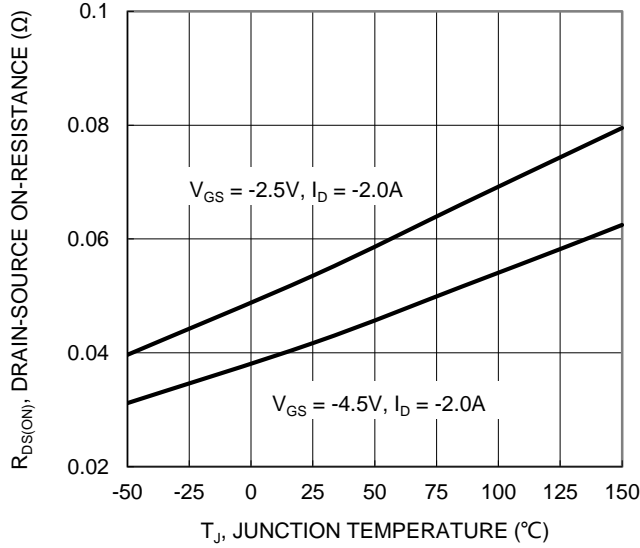


Figure 7. On-Resistance Variation with Junction Temperature

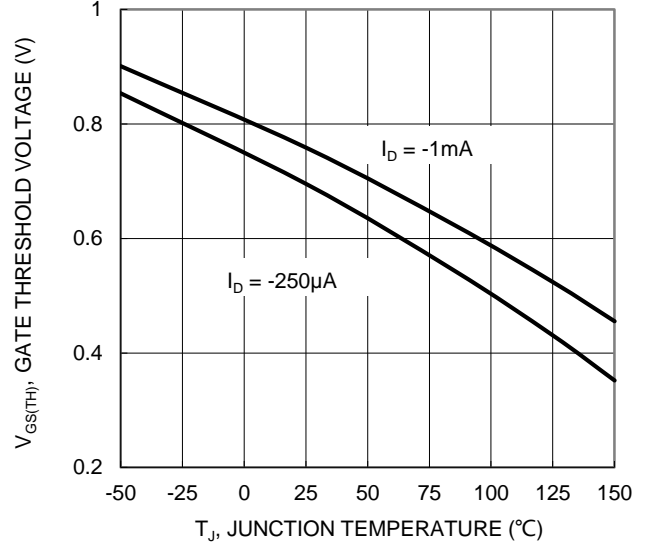


Figure 8. Gate Threshold Variation vs. Junction Temperature

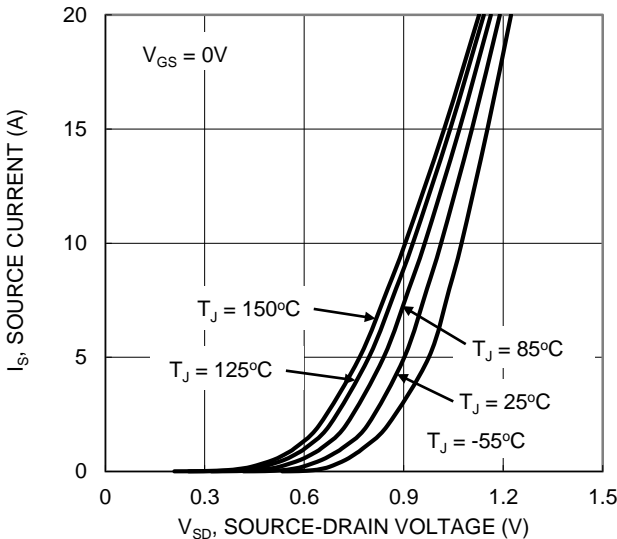


Figure 9. Diode Forward Voltage vs. Current

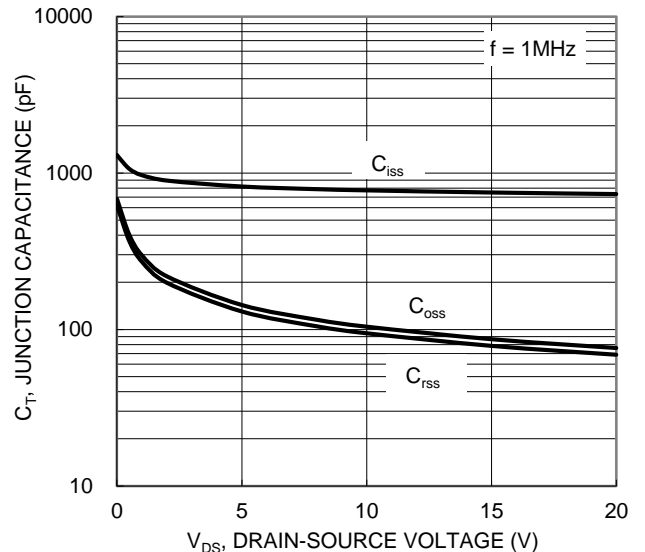


Figure 10. Typical Junction Capacitance

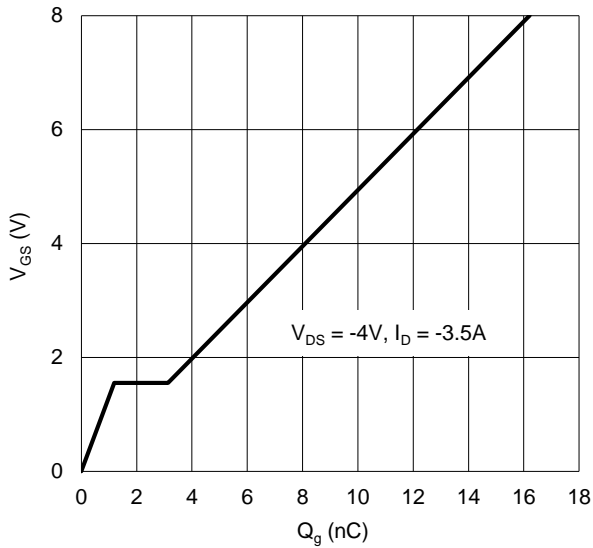


Figure 11. Gate Charge

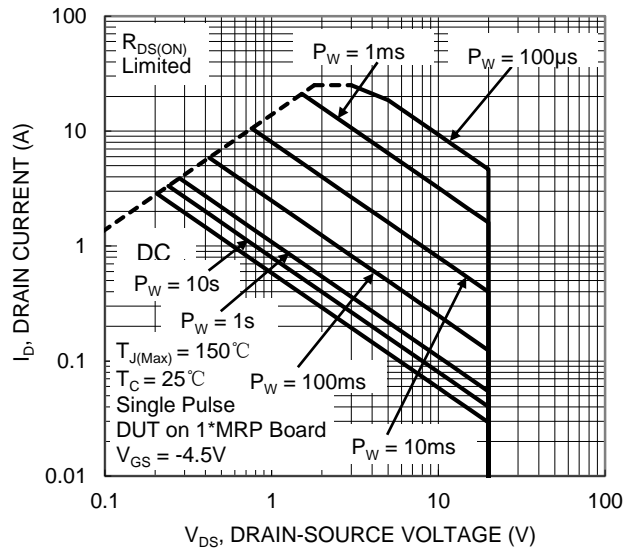


Figure 12. SOA, Safe Operation Area

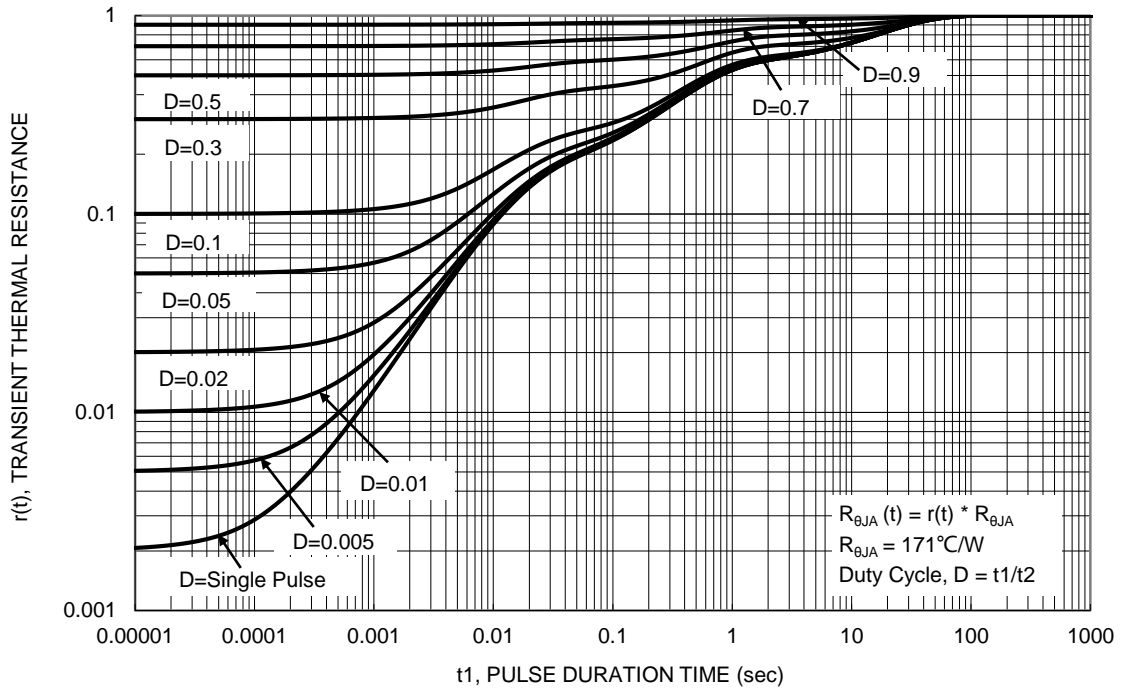
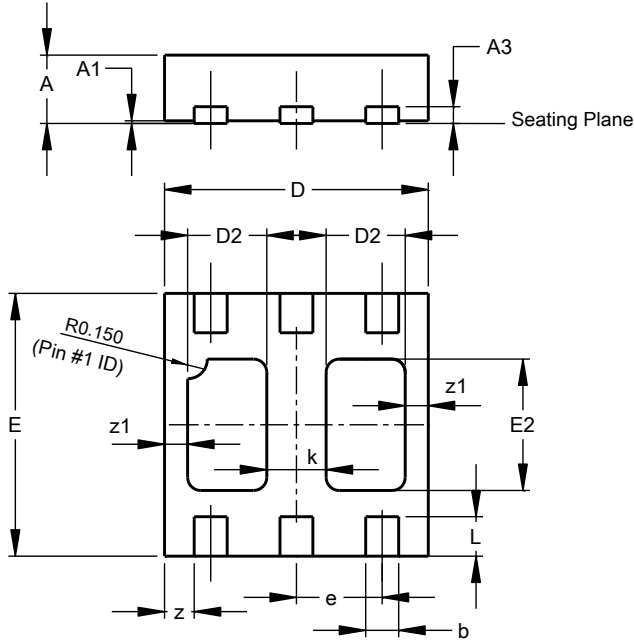


Figure 13. Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### U-DFN2020-6 (Type B)

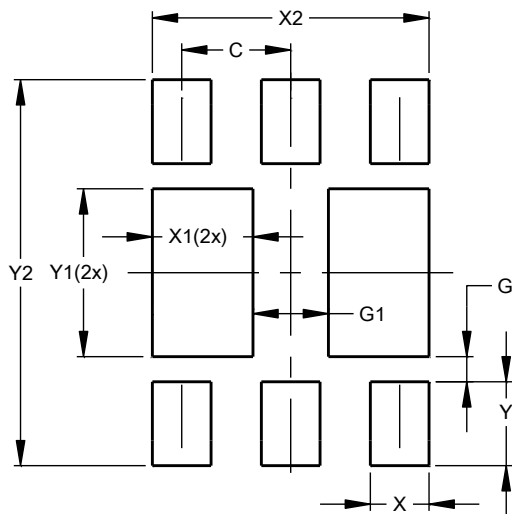


U-DFN2020-6 Type B			
Dim	Min	Max	Typ
A	0.545	0.605	0.575
A1	0.00	0.05	0.02
A3	-	-	0.13
b	0.20	0.30	0.25
D	1.95	2.075	2.00
D2	0.50	0.70	0.60
e	-	-	0.65
E	1.95	2.075	2.00
E2	0.90	1.10	1.00
k	-	-	0.45
L	0.25	0.35	0.30
z	-	-	0.225
z1	-	-	0.175
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### U-DFN2020-6 (Type B)



Dimensions	Value (in mm)
C	0.650
G	0.150
G1	0.450
X	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300

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